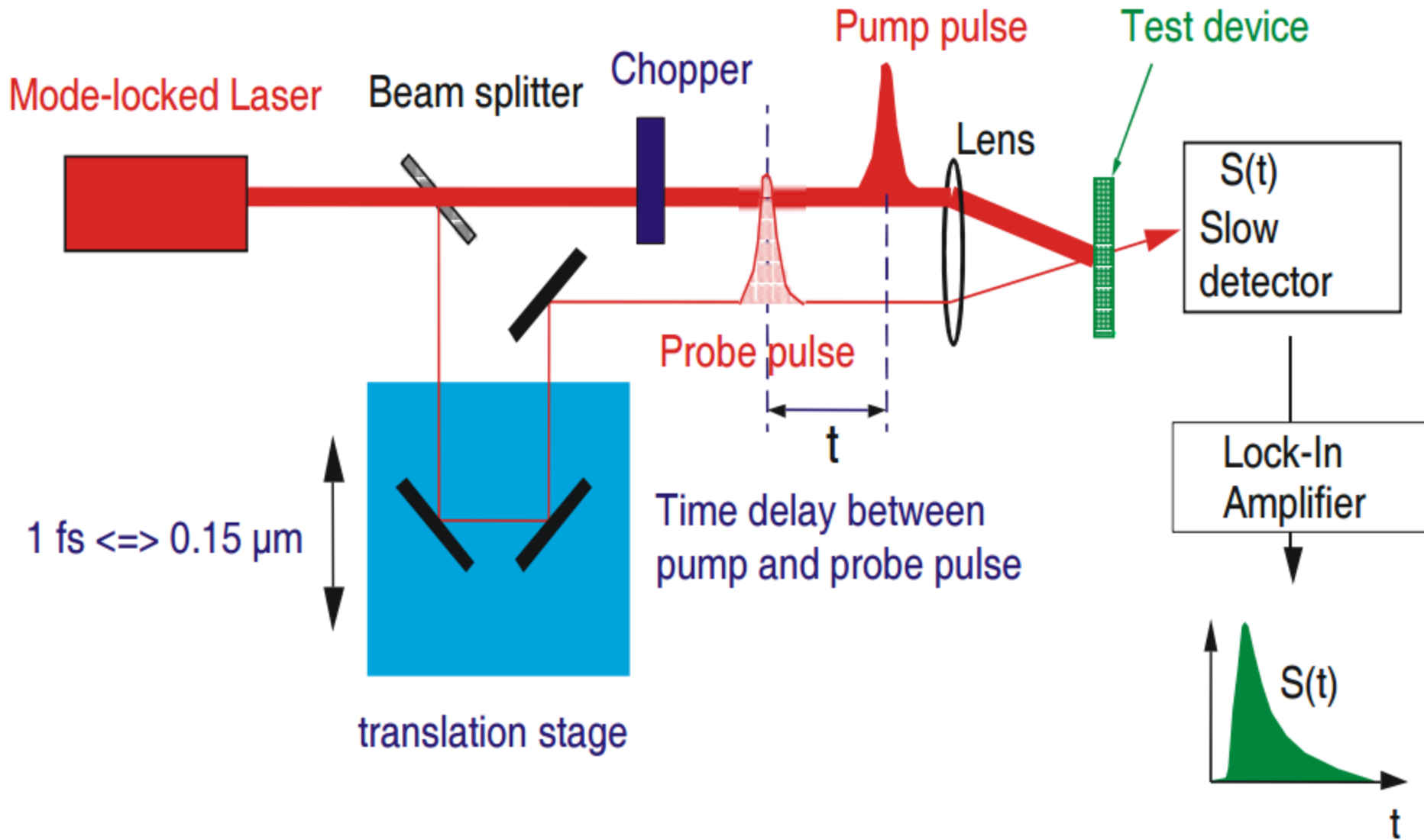


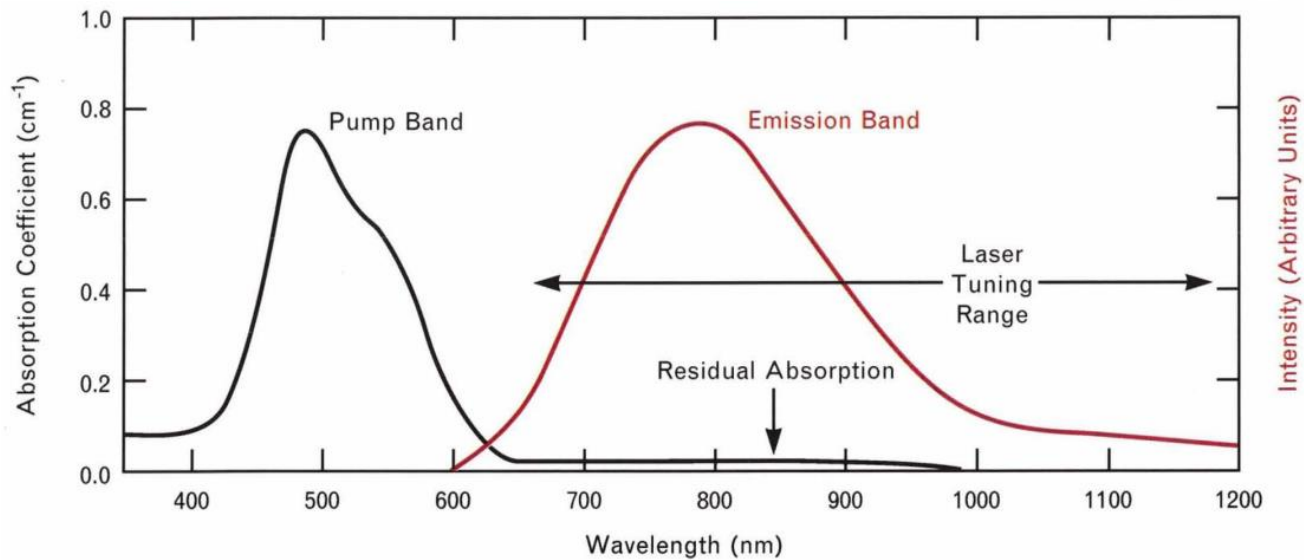
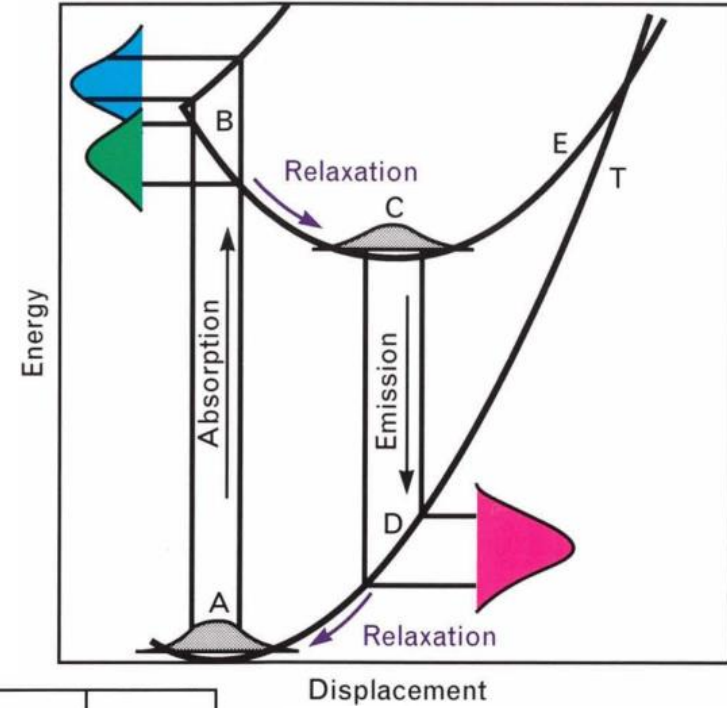
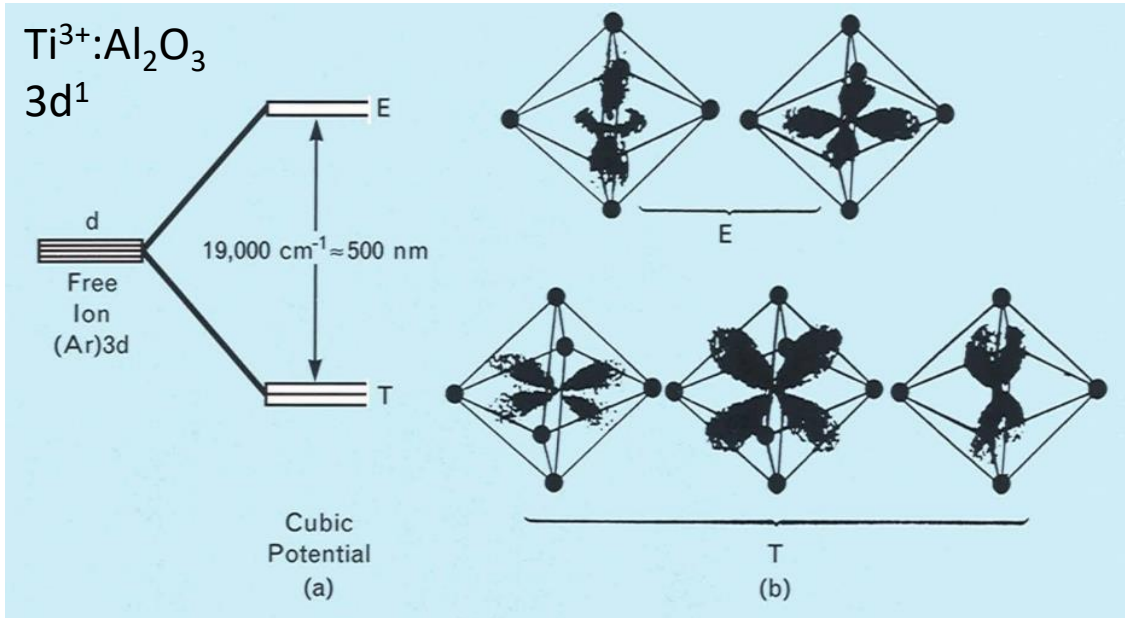
Time-resolved spectroscopy



Time-resolved absorption/reflectivity/luminescence ...

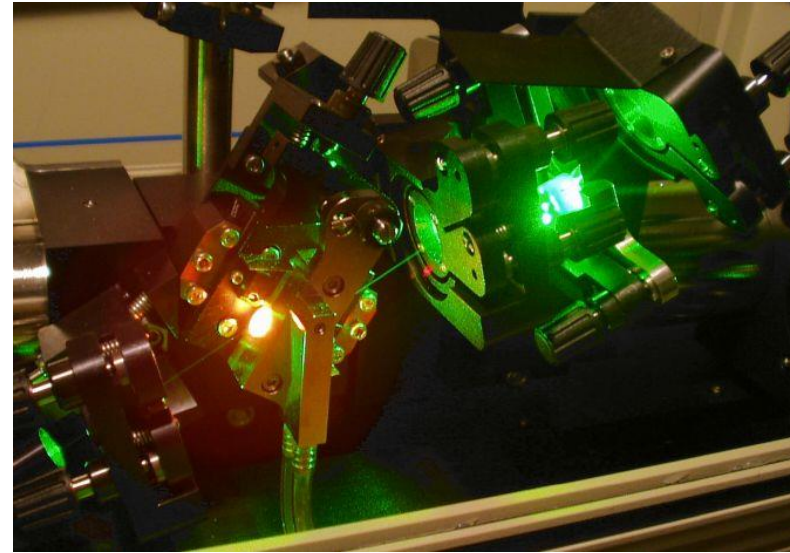
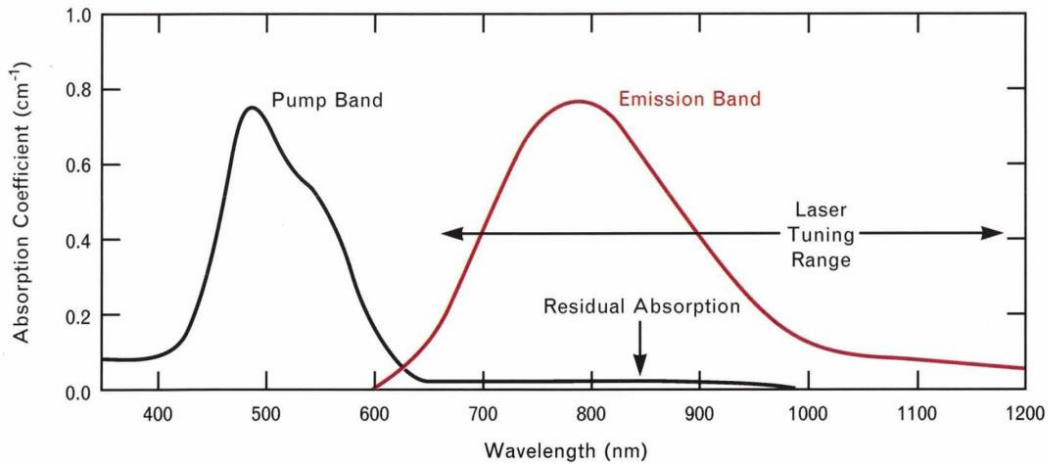


Ti:sapphire LASER

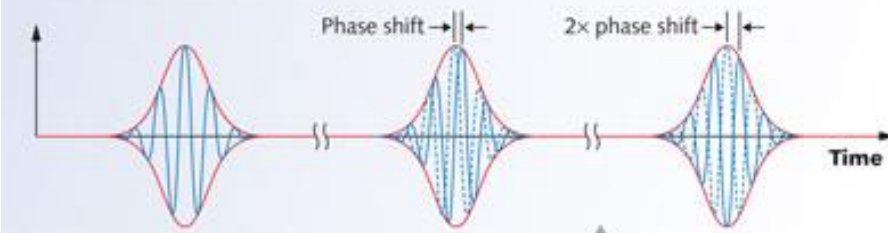


Ti:sapphire LASER

Pump: green, lasing: NIR

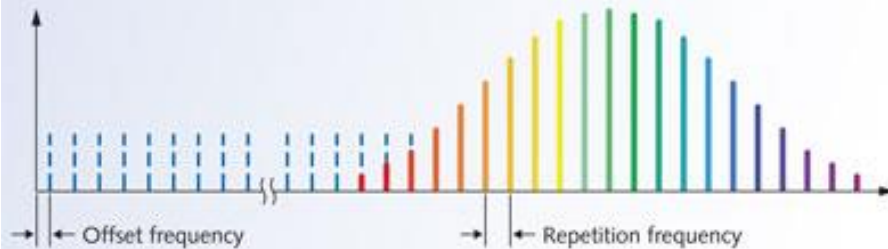


Time domain - femtosecond pulses



Fourier transformation

Frequency domain - frequency comb



Central wavelength: 800 nm (375 THz)

Pulse width: 10-100 fs

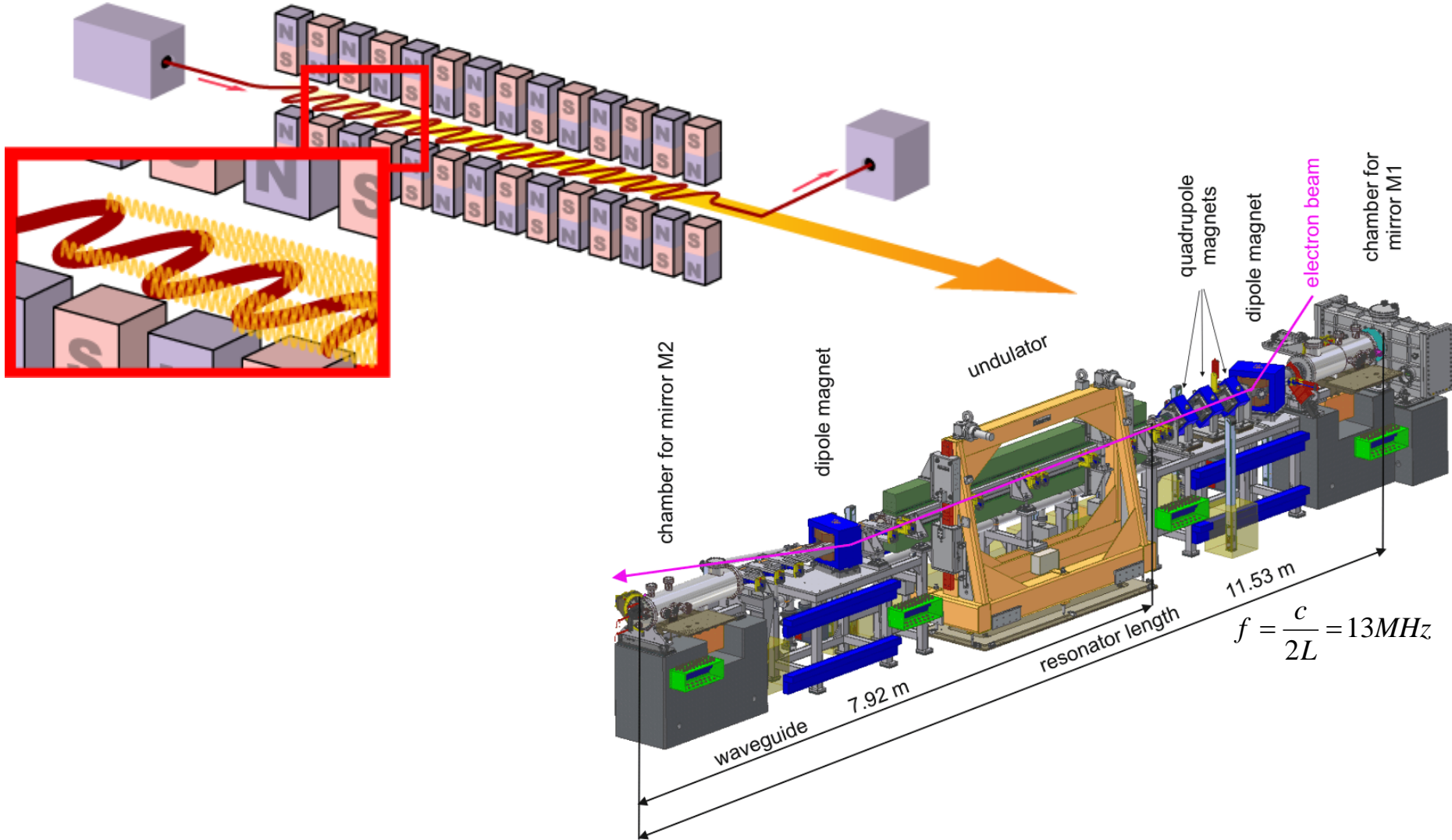
Repetition rate: 80 MHz ($\frac{c}{2L}$), resonator: ~ 2 m

Free Electron LASER (FEL)

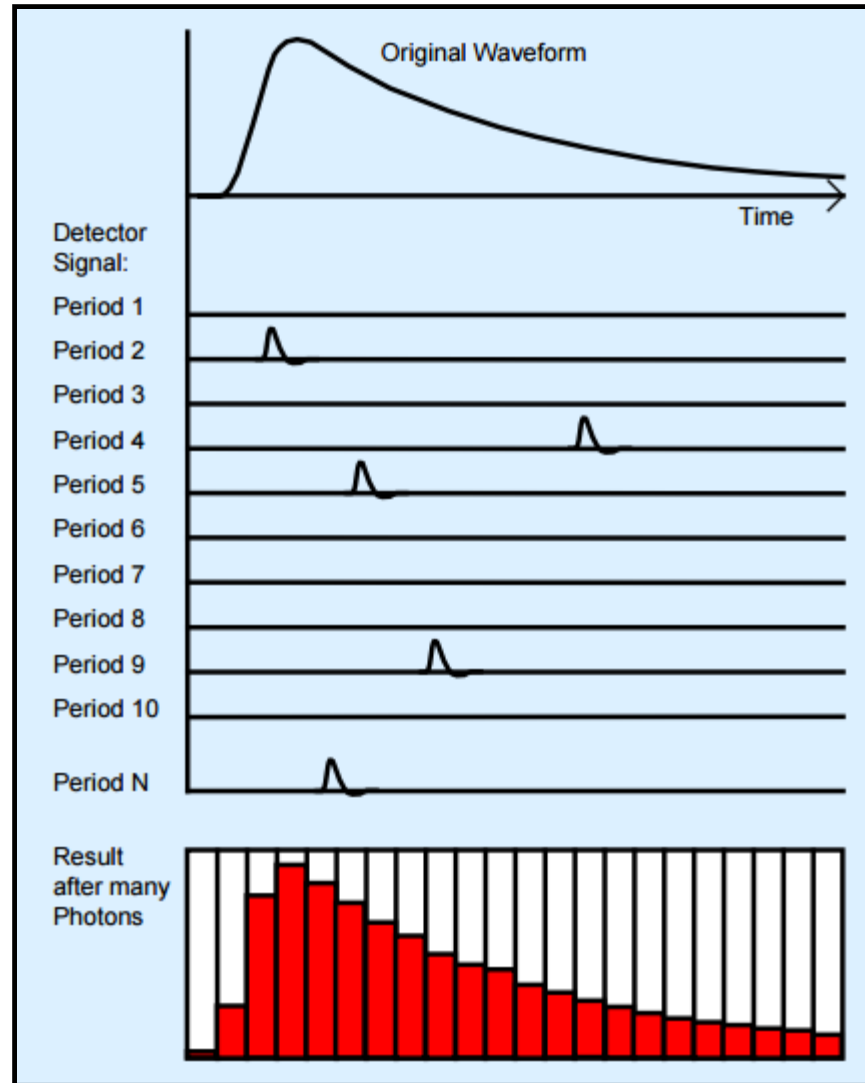
Lasing medium: relativistic free electrons traveling in an undulator

Interaction between the electron beam and the E-field of the radiation leads to bunching and coherent radiation

Most widely tuneable LASER: from microwave to X-ray



Time-Correlated Single Photon Counting



Ahmed Zewail - Facts



Ahmed H. Zewail

Born: 26 February 1946, Damanhur, Egypt

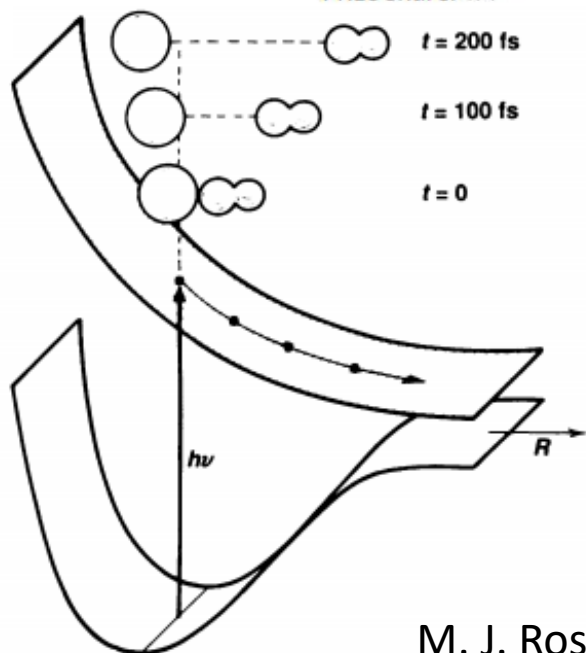
Died: 2 August 2016

Affiliation at the time of the award: California Institute of Technology (Caltech), Pasadena, CA, USA

Prize motivation: "for his studies of the transition states of chemical reactions using femtosecond spectroscopy"

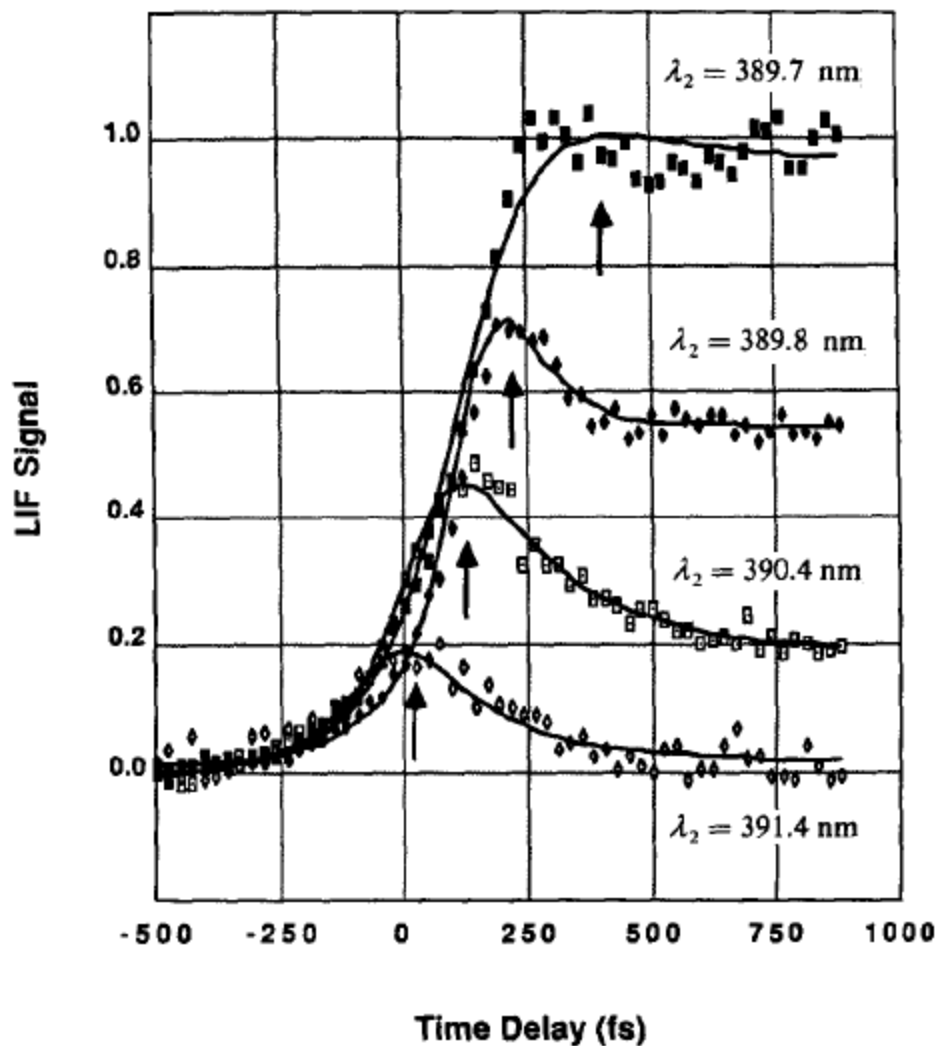
Field: chemical kinetics, physical chemistry

Prize share: 1/1

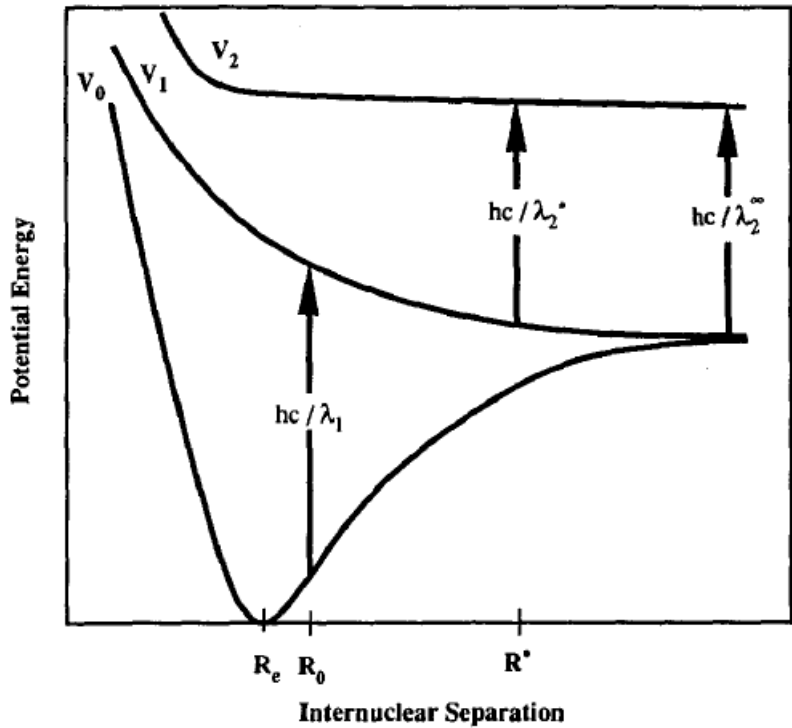


LIF: Laser Induced Fluorescence

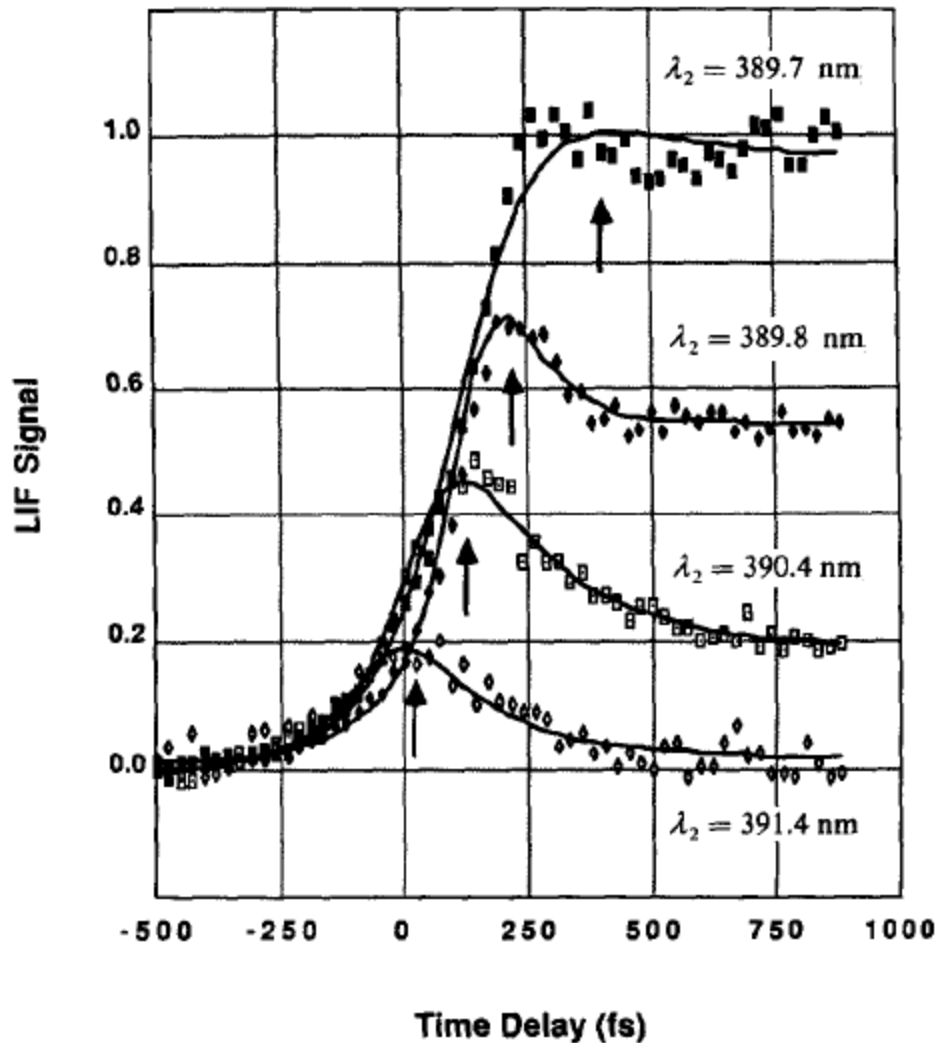
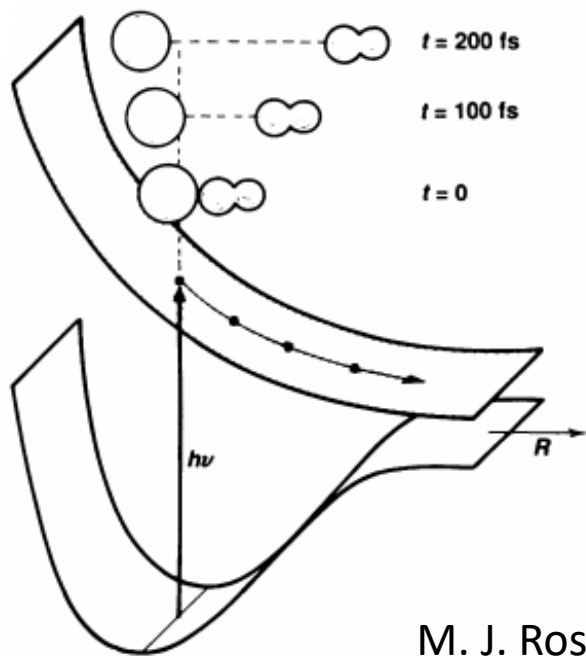
Fluorescence signal is measured after absorption

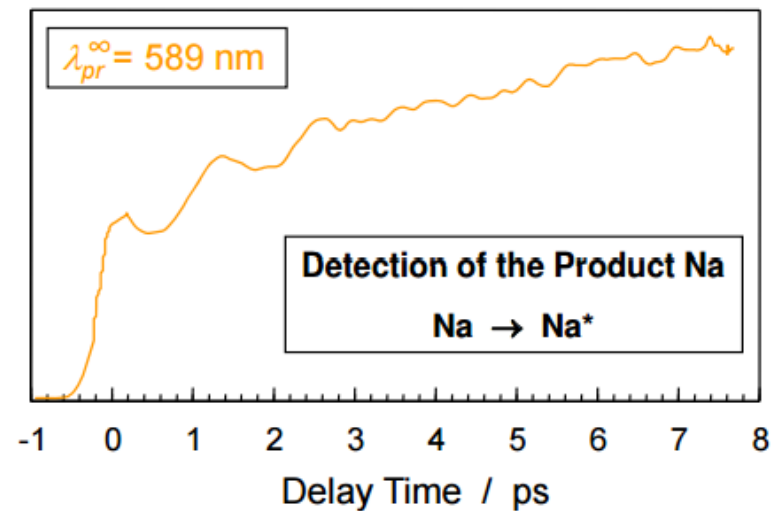
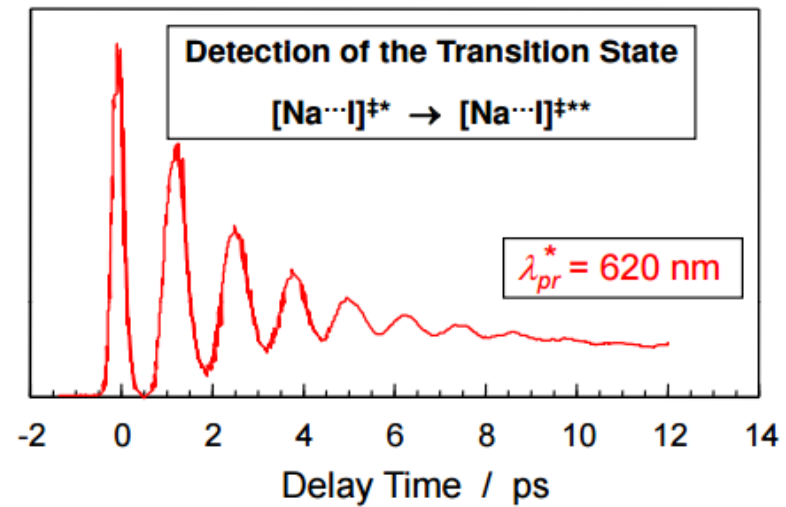
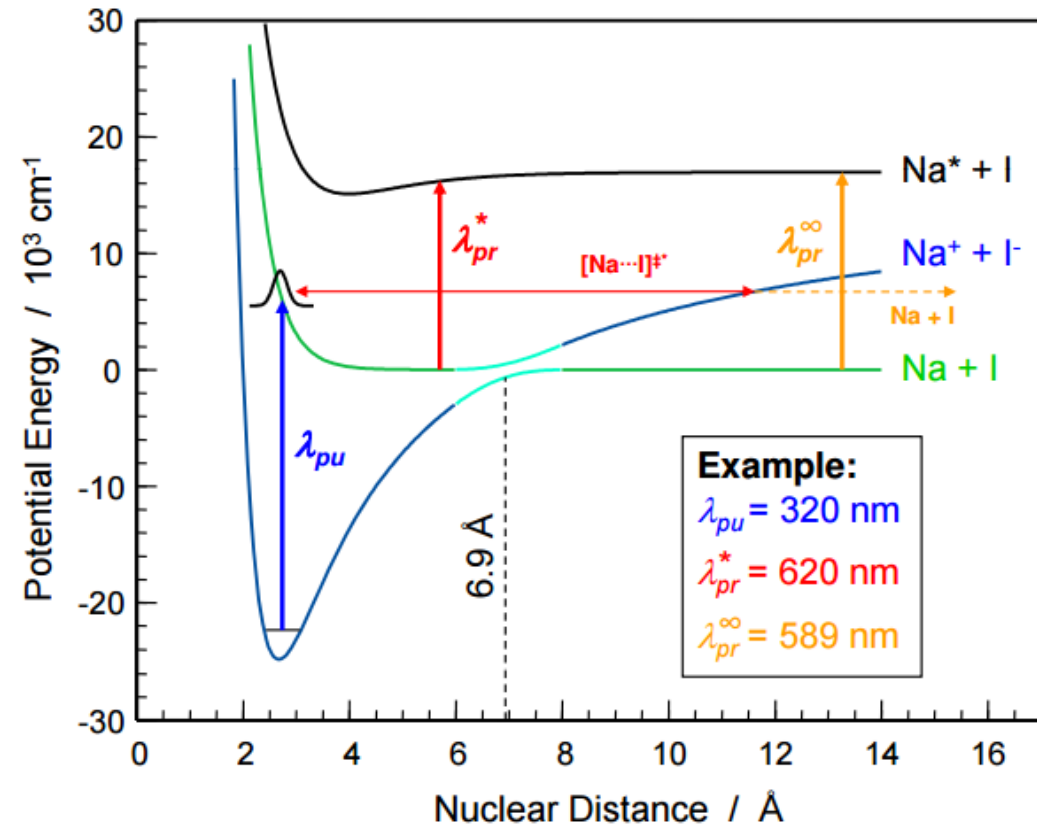


M. J. Rosker, M. Dantus, A. H. Zewail, J. Chem. Phys. **89**, 6113 (1988).



LIF: Laser Induced Fluorescence
 Fluorescence signal is measured after absorption

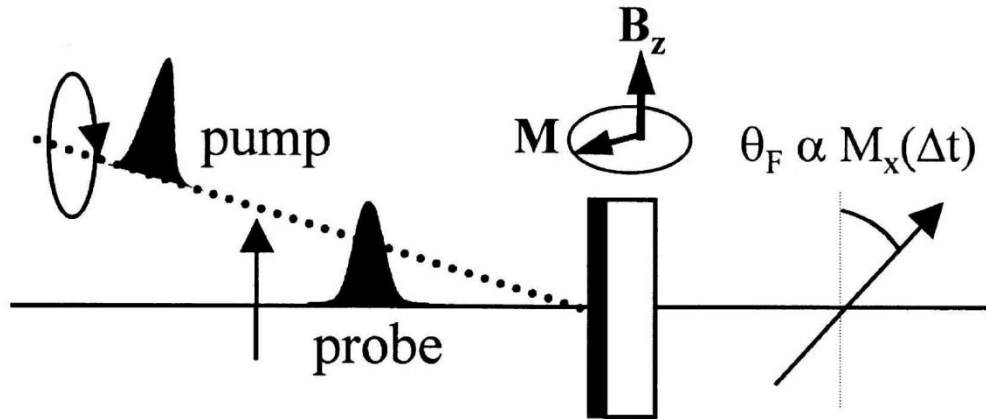




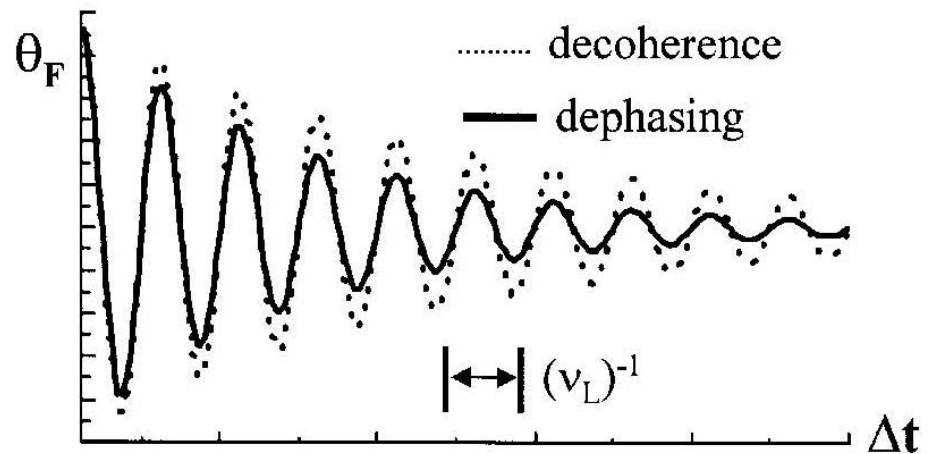
M. J. Rosker, M. Dantus, A. H. Zewail, J. Chem. Phys. **89**, 6113 (1988).

A. Materny, Jacobs University Bremen (2009).

Time-domain magneto-optical spectroscopy



$$\theta_F(\Delta t) = A e^{-\Delta t/T_2^*} \cos(2\pi\nu_L \Delta t)$$



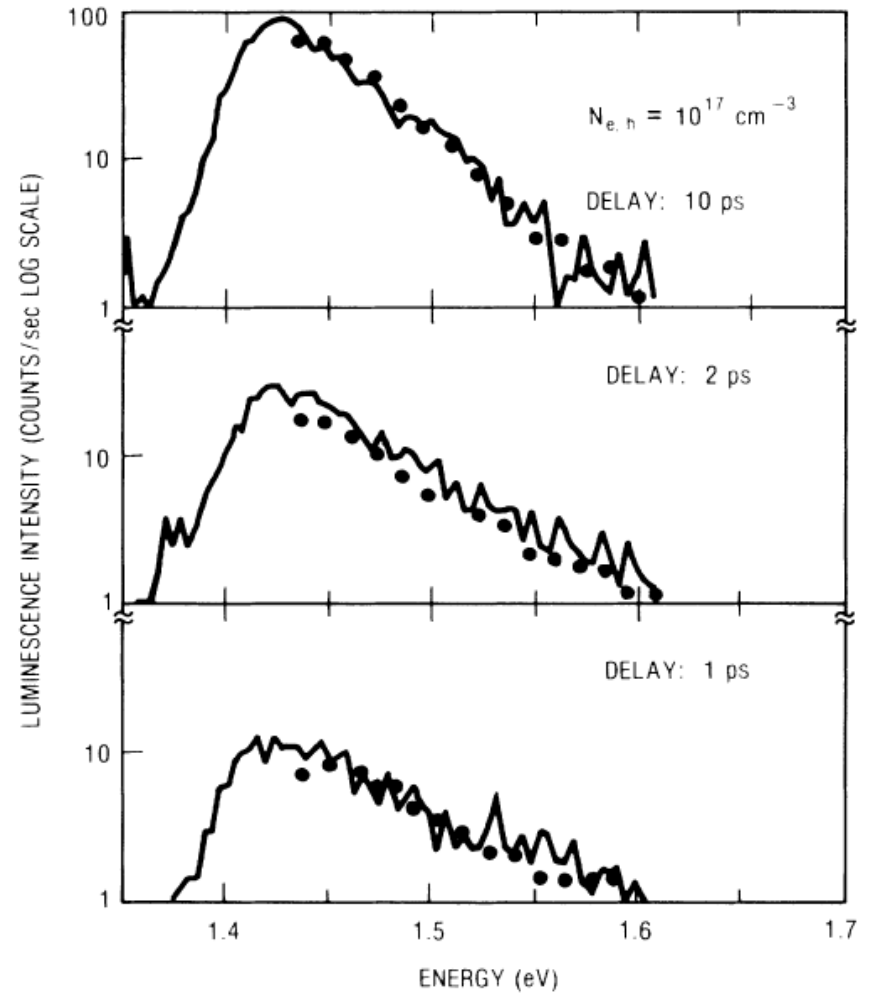
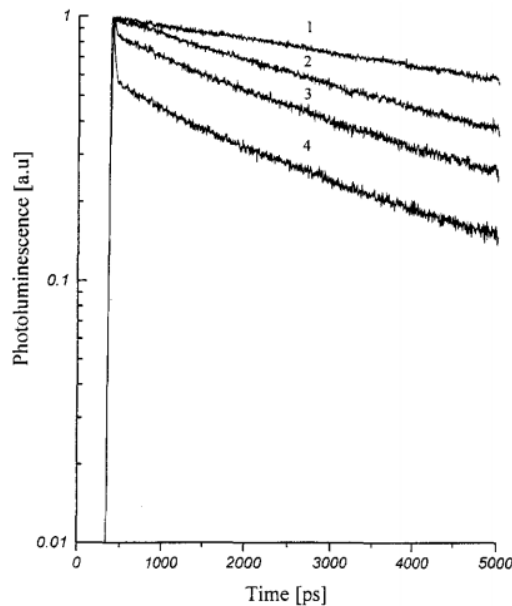
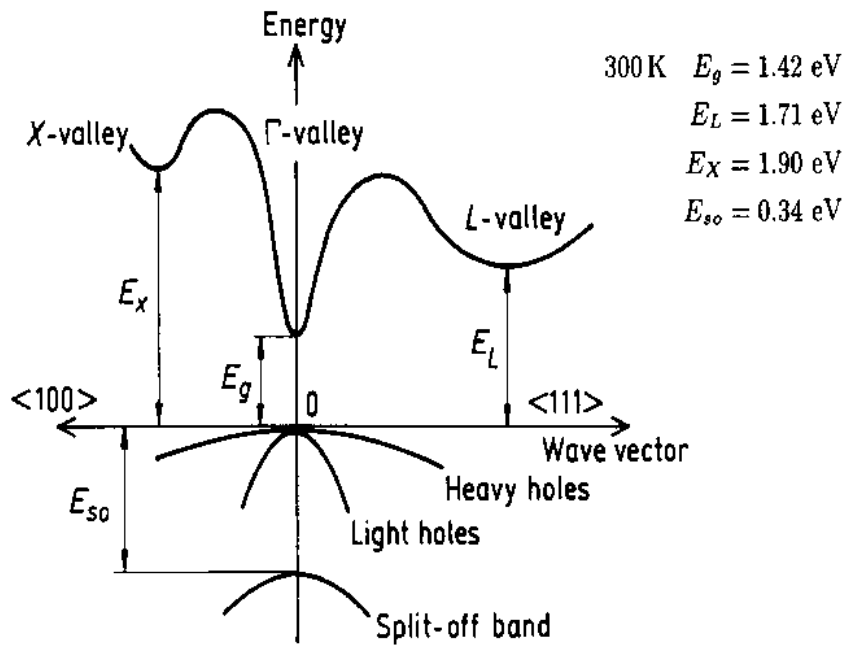
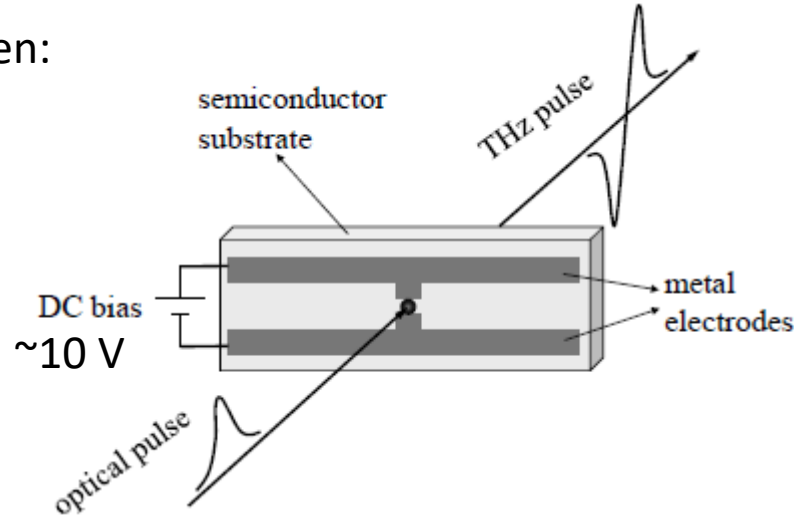


Fig. 1. Semilog plots of time resolved photoluminescence (PL) measured at various photon energies of $0.5 \mu\text{m}$ GaAs crystal. Curves 1, 2, 3 and 4 correspond to PL energy of: 1.43 eV, 1.49 eV, 1.57 eV, 1.65 eV, respectively.

Terahertz sugárzás keltése

Dipól antenna LT-GaAs-en:



LT-GaAs:

- recombináció: $\tau_{rec}=0.3$ ps
- mobilitás: $\mu=200$ cm²/Vs ($\tau_{scat}=30$ fs)
- gap: $E_g=840$ nm

Ti:Sapphire LASER:

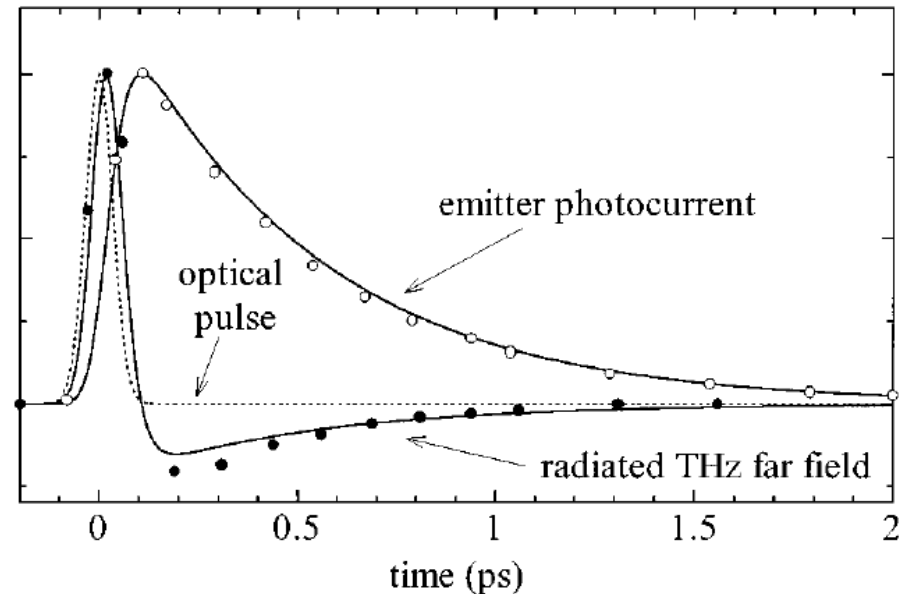
- központi hullámhossz: $\lambda=800$ nm
- impulzus szélesség: $\tau<100$ fs

$$E_{THz} \propto \frac{\partial j}{\partial t}$$

$$j(t) = \int P(t-t')[en(t')v(t')]dt'$$

$$[...] = e \exp(-t'/\tau_{rec}) \mu (1 - \exp(-t'/\tau_{scat})) \frac{V}{d}$$

$$V_{Max} \sim \frac{1}{\tau_{rec}} = 3 \text{ THz}$$



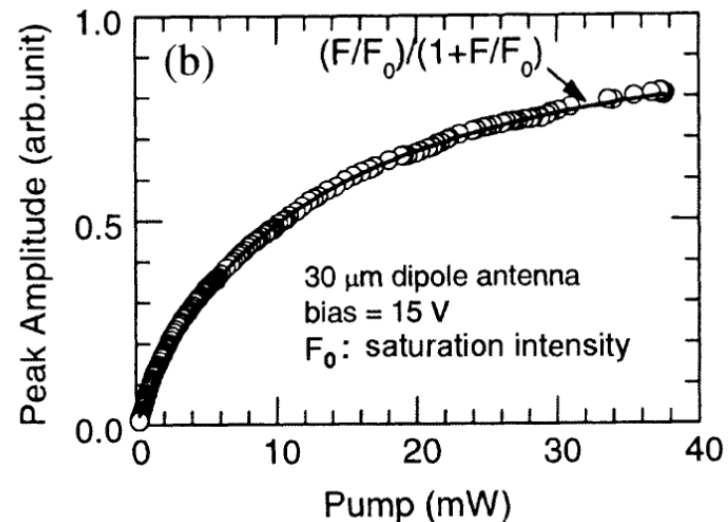
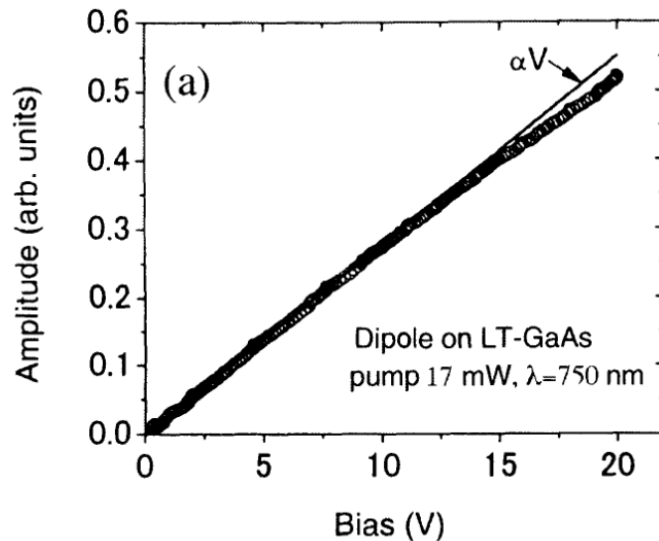
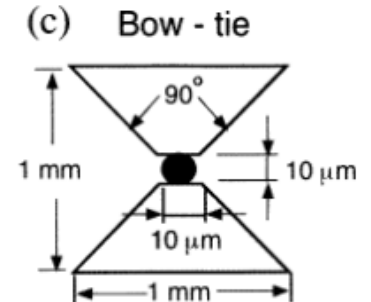
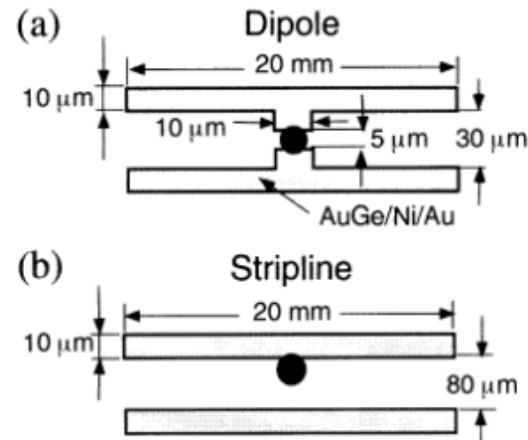
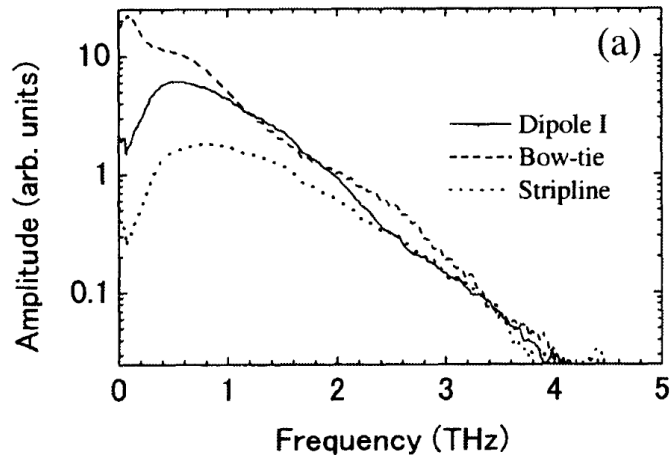
Y. S. Lee: Principles of Terahertz Science and Technology Springer, Berlin (2009)

L. Duvillaret et al. *IEEE J. Sel. Top. Quant. Electronics.* 7 615 (2001)

Terahertz sugárzás keltése

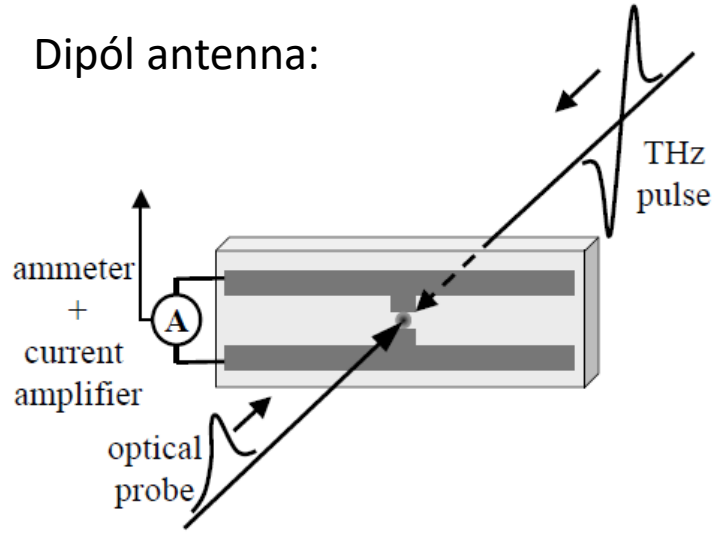
Ti:Sapphire
@ 800nm
20 mW

60 V → THz sugárzás
2-3 μ W

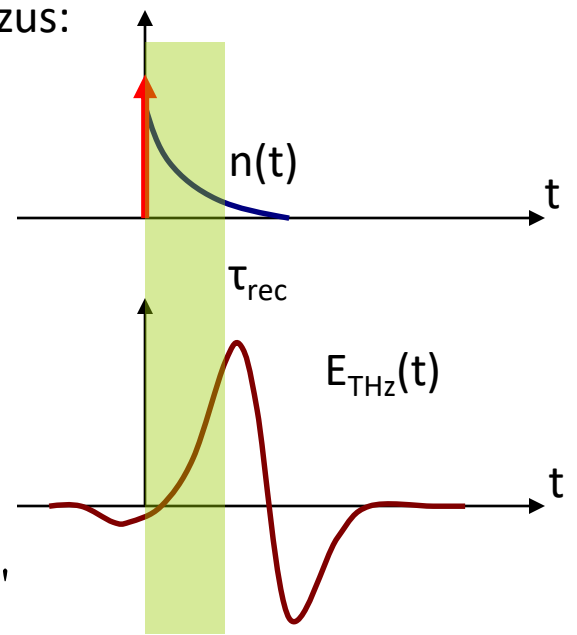


Terahertz sugárzás koherens detektálása

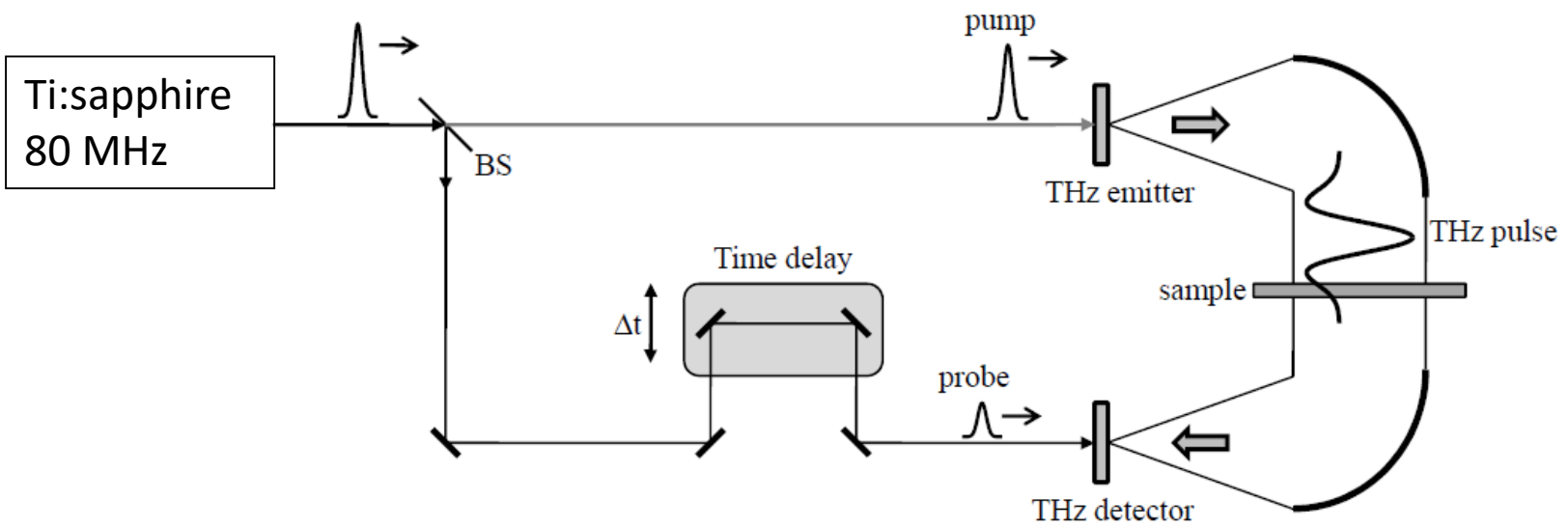
Dipól antenna:



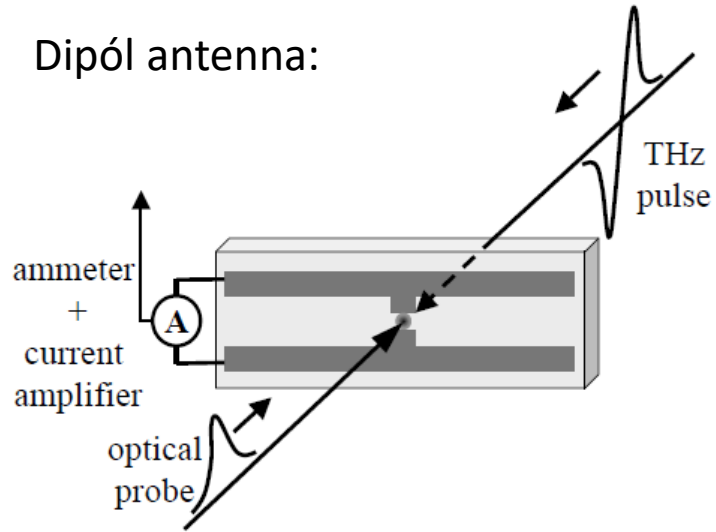
δ -impulzus:



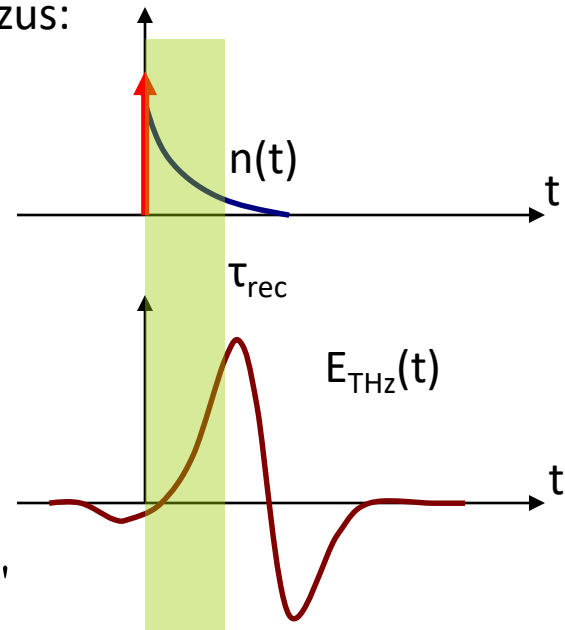
$$j_D(t) = e \exp(-t / \tau_{rec}) \int_0^t \exp(-t' / \tau_{scat}) \frac{e}{m} E_{THz}(t - t') dt'$$



Terahertz sugárzás koherens detektálása



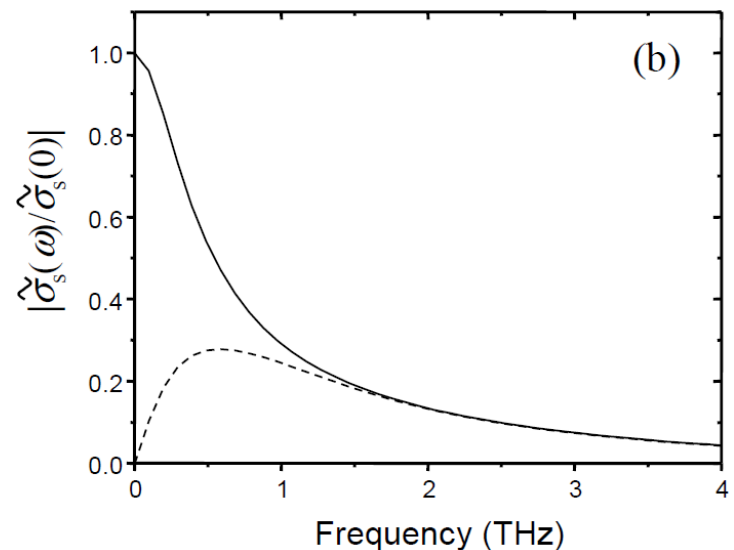
δ -impulzus:



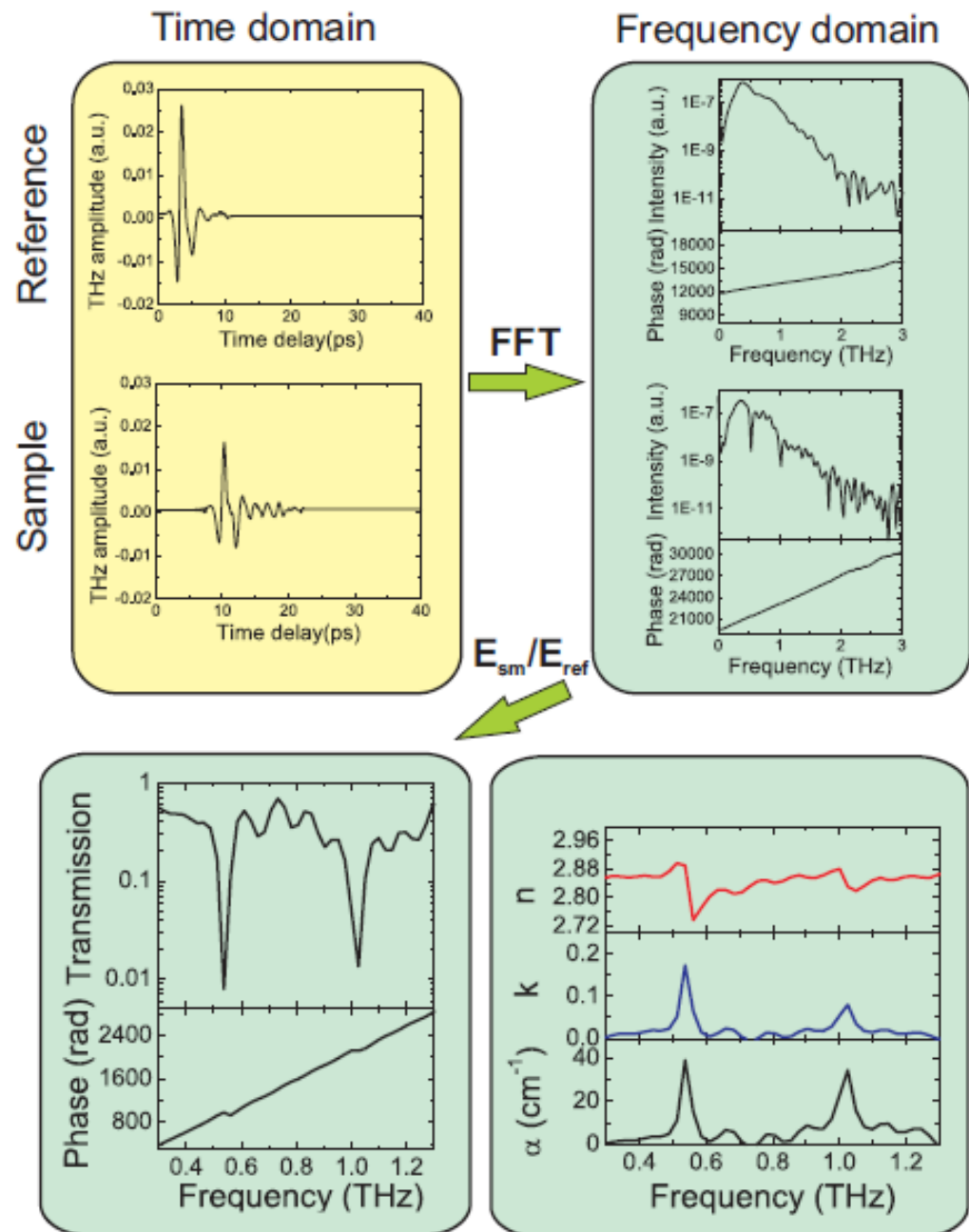
$$j_D(t) = e \exp(-t / \tau_{rec}) \int_0^t \exp(-t' / \tau_{scat}) \frac{e}{m} E_{THz}(t - t') dt'$$

Nagy frekvenciás korlát: $1/\tau_{rec} \sim 3$ THz

Alacsony frekvenciás limit: diffrakció
limitált leképezés



Komplex THz spektrum



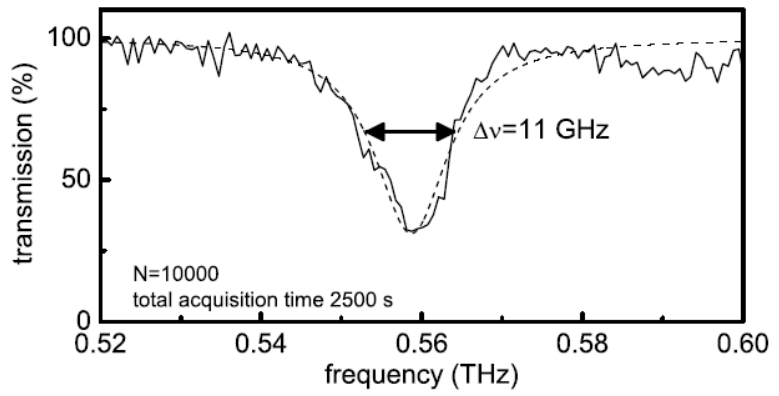
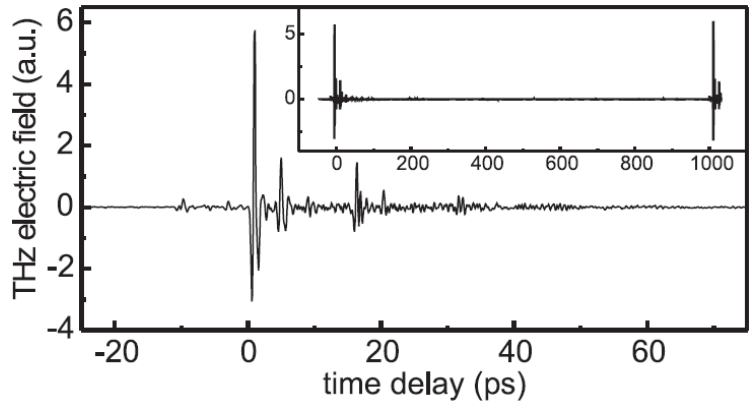
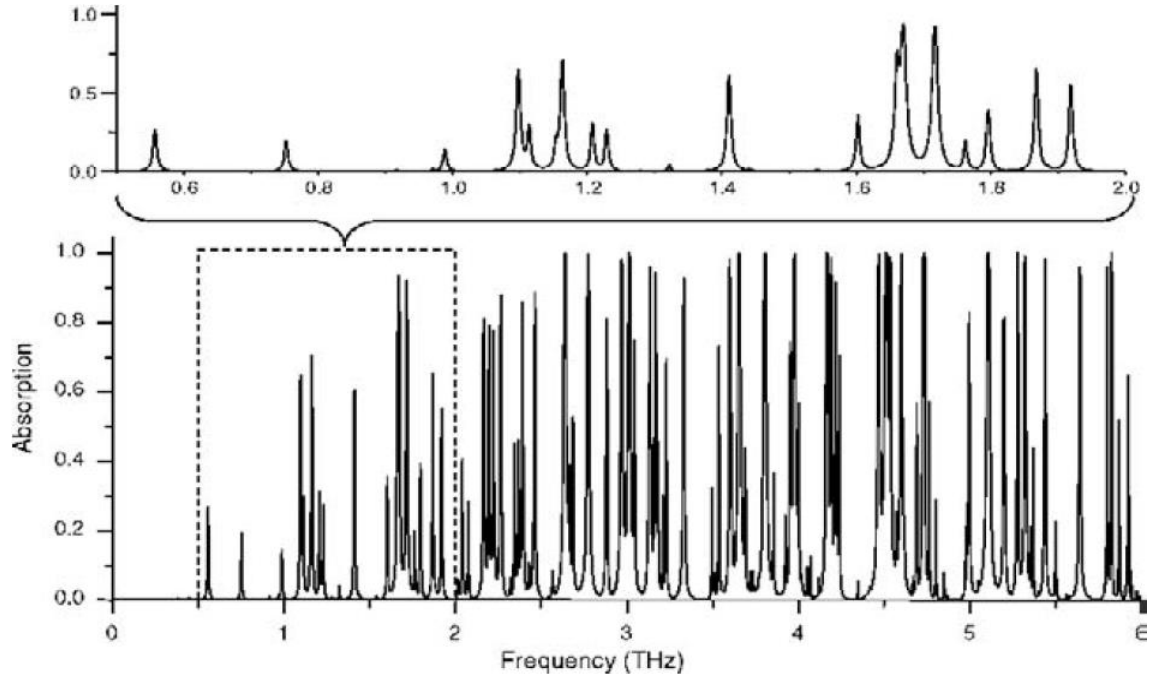
Molekulák ujjlenyomatai: rotációs spektrum

Molekulák forgási energiája:

$$E \sim \frac{\hbar^2}{2MR^2} \sim 1\text{THz}$$

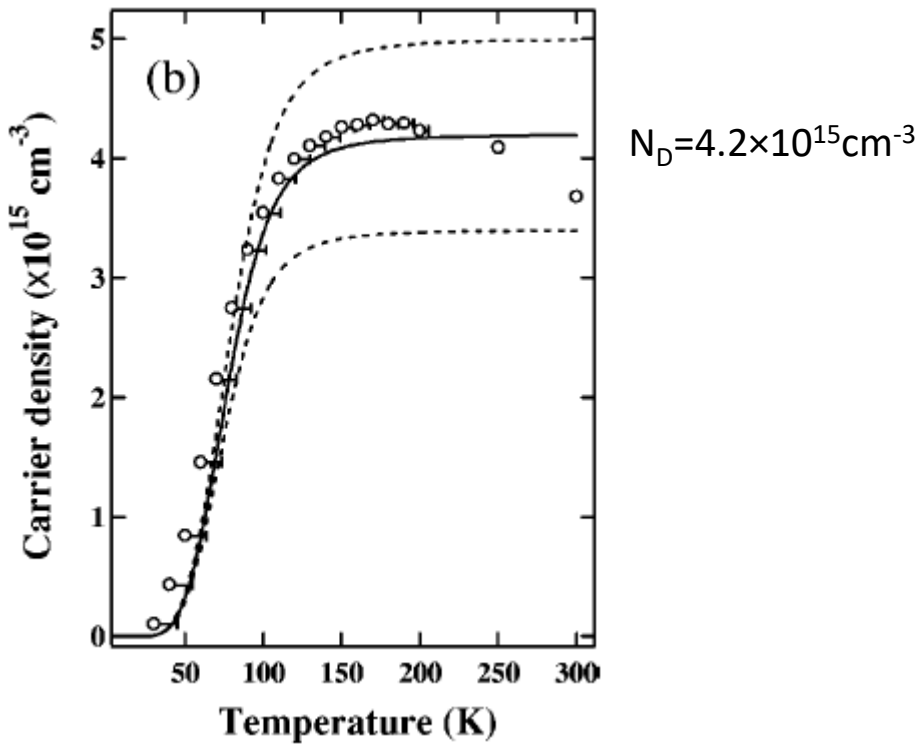
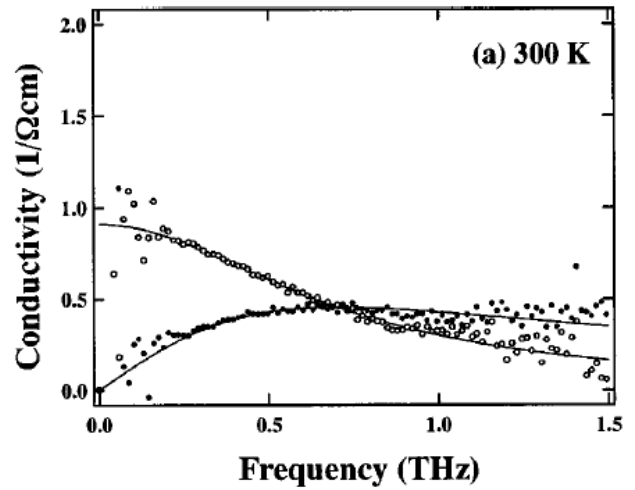
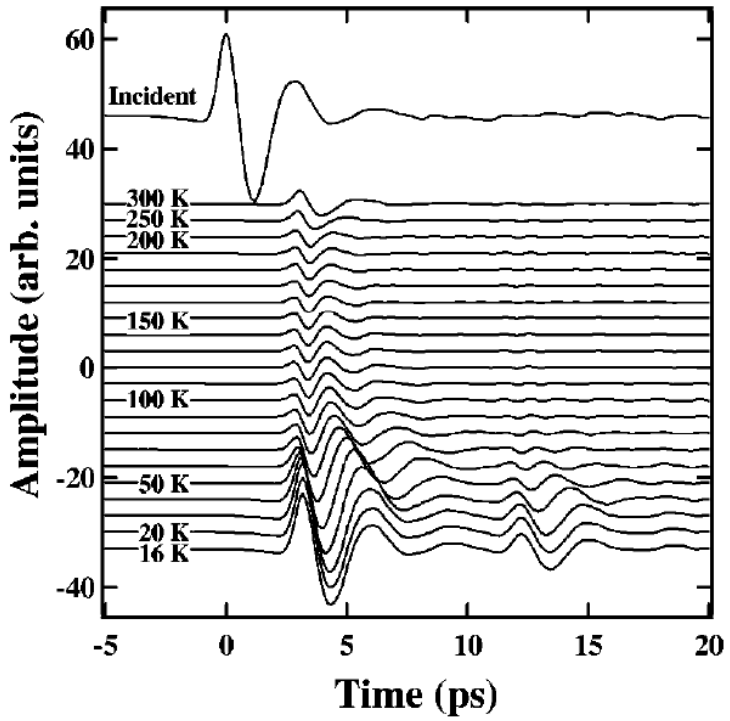
Víz gőz rotációs spektruma

Nagyfelbontású (~1GHz)
THz spektroszkópia:



Félvezető szeletek érintésmentes minősítése

Adalékolt p-Si szelet

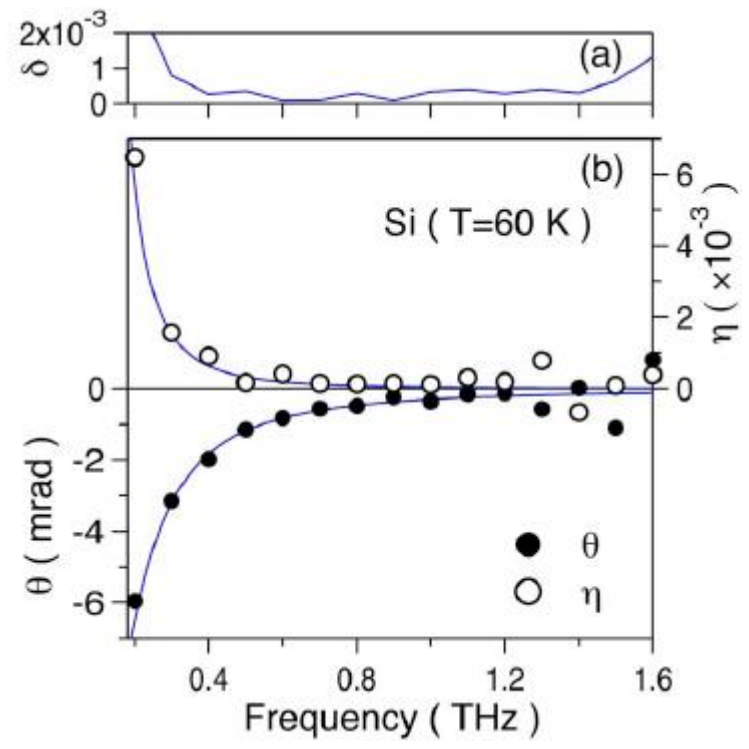
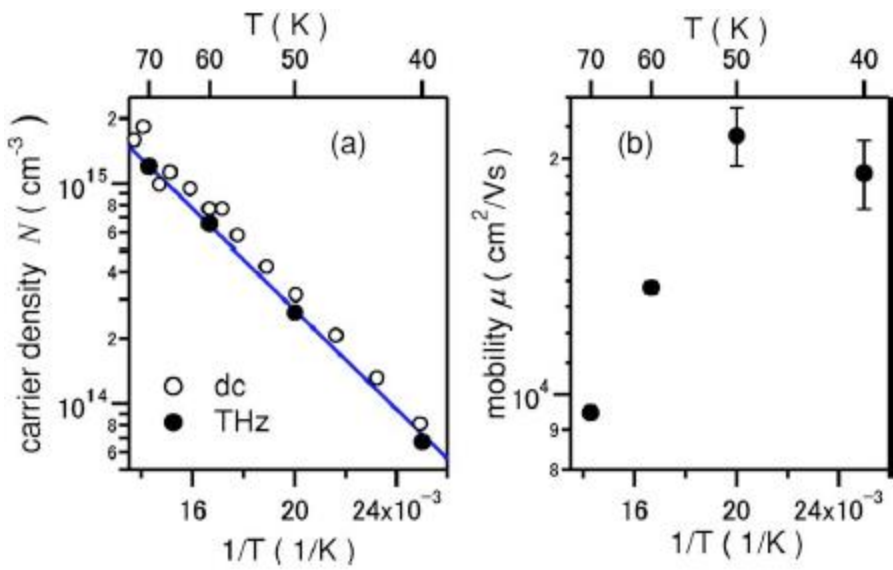


Félvezető szeletek érintésmentes minősítése

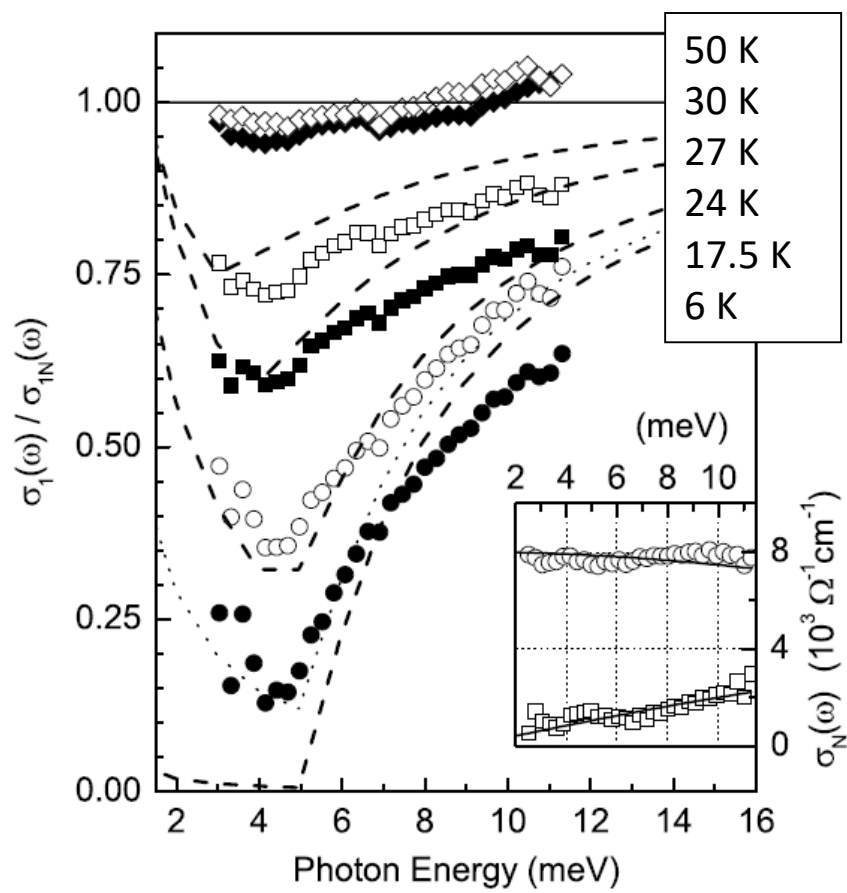
Adalékolt n-Si szelet

$$E_y(\omega, B) \approx E_0(\omega) \exp \left[-i\omega \left(t - \frac{\hat{N}(0)}{c} d \right) \right] \times (\sin \theta + i\eta \cos \theta) = E_x(\omega, 0) (\sin \theta + i\eta \cos \theta),$$

$$\theta + i\eta = -\frac{\omega}{2c} \frac{i\epsilon_{xy}}{\sqrt{\epsilon_{xx}}} d$$

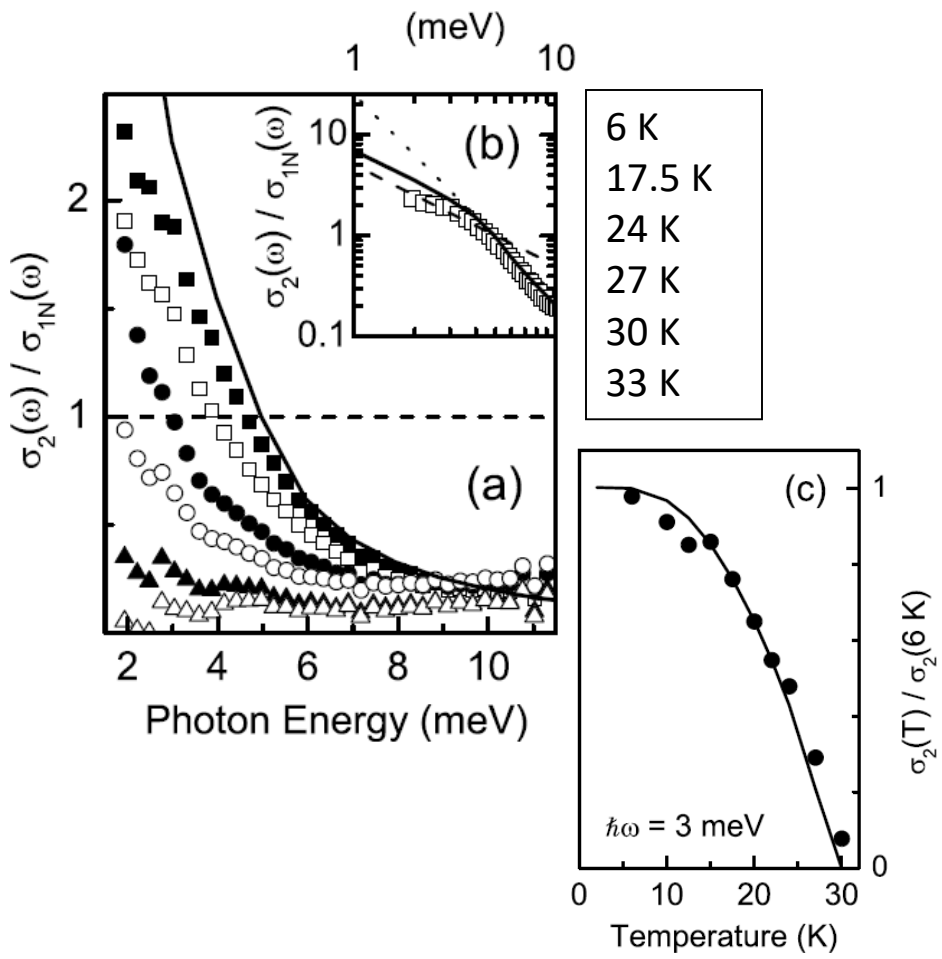


Szupravezetők elektrodinamikája: MgB_2



BCS fit: $2\Delta_0=5$ meV
 Gyenge csatolás: $2\Delta_0=3.5k_B T_C=9$ meV

Gap alatt kvázirészecske gerjesztés



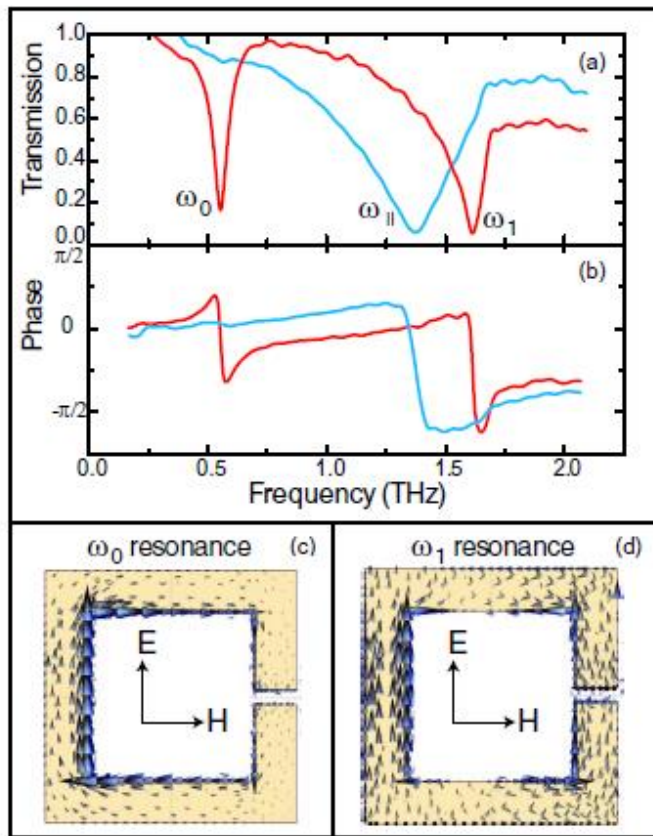
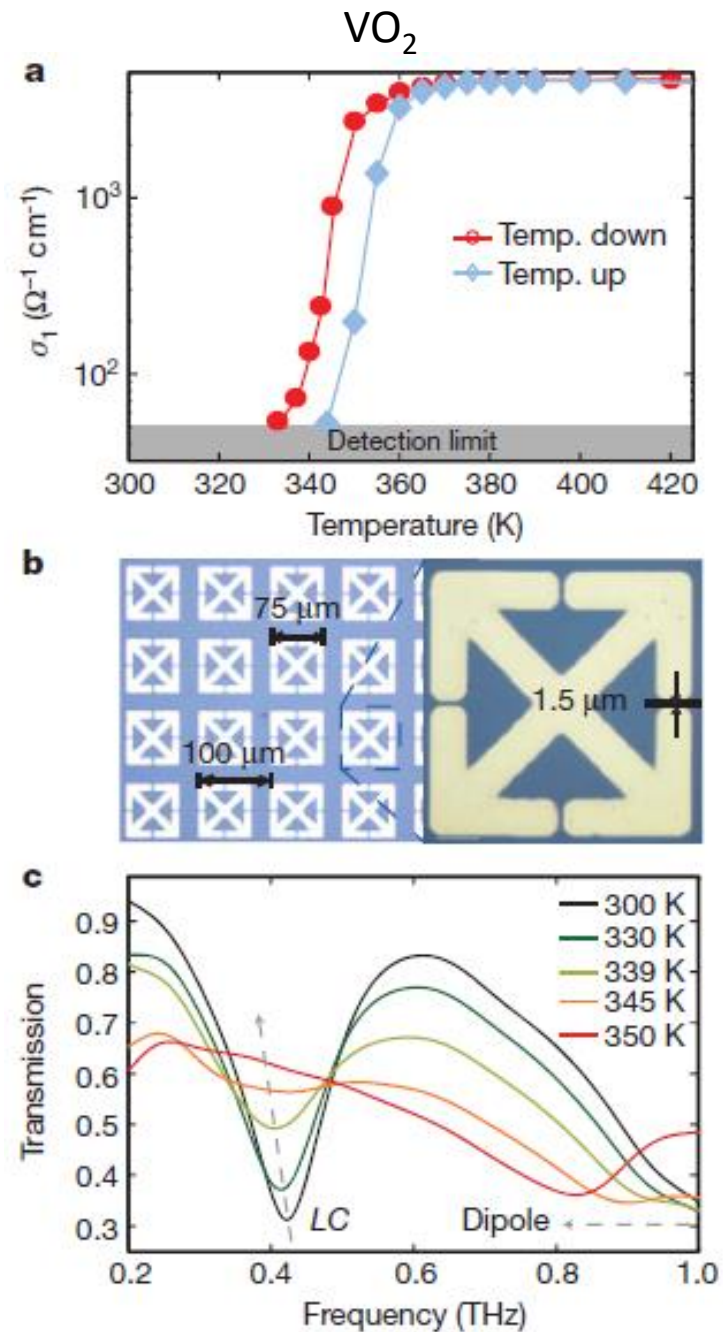
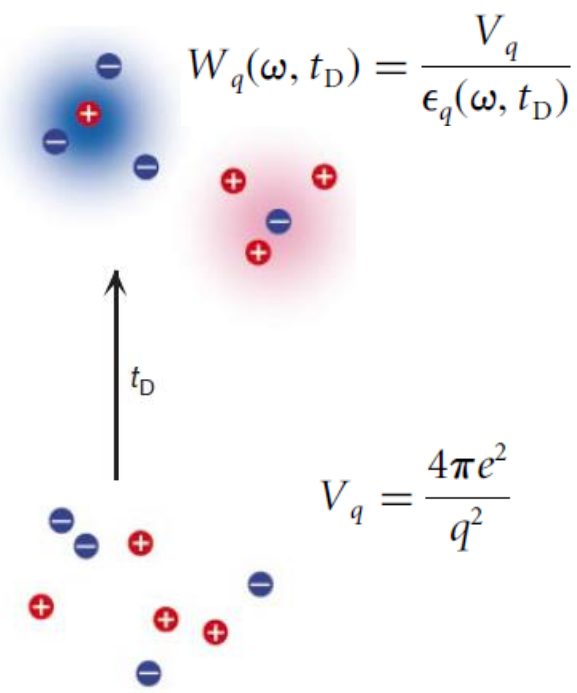


FIG. 1 (color online). The frequency dependent transmission spectra $T(\omega)$ of the SRR sample is shown in (a), and in (b) the corresponding phase of the transmission is shown. In (a) and (b), the electric field is perpendicular to the SRR gap [red (dark) curves] and parallel to the SRR gap [blue (light) curves] at normal incidence. (c) and (d) are the surface current densities for the ω_0 (0.5 THz) and ω_1 (1.6 THz) resonances, respectively, as calculated by simulation. See the text for details.

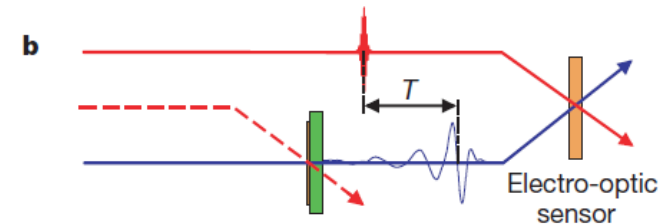
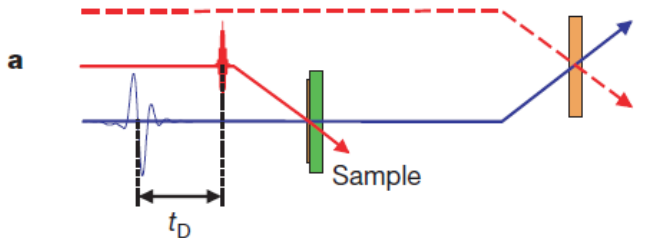


Coulomb gáz időfejlődése

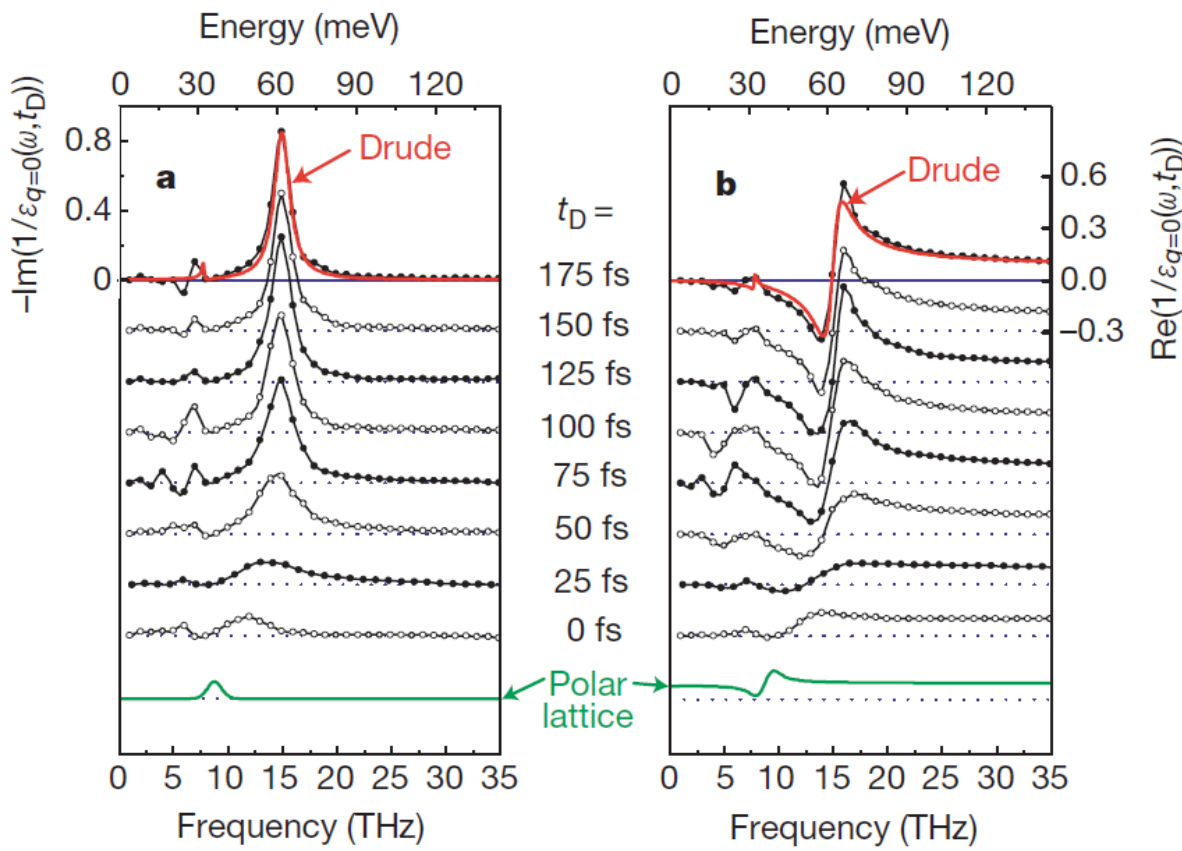


$$W_q(\omega, t_D) = \frac{V_q}{\epsilon_q(\omega, t_D)}$$

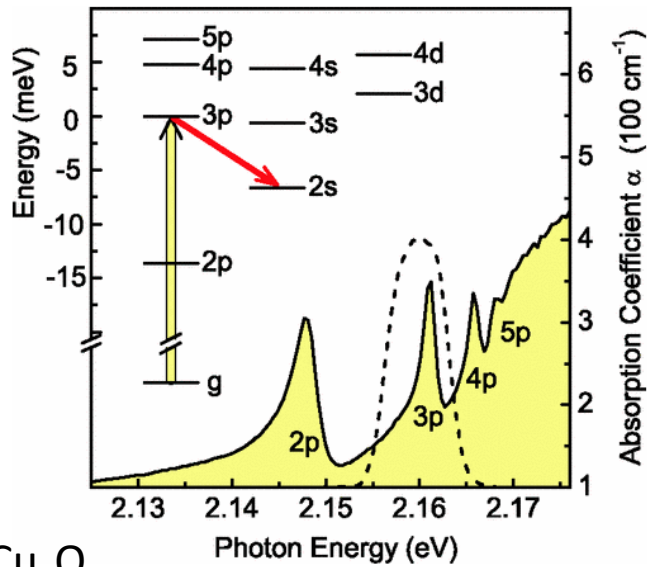
$$V_q = \frac{4\pi e^2}{q^2}$$



NIR pumpa – THz próba spektroszkópia



Wannier-Mott excitons: $E_B = \frac{\mu e^4}{2\hbar^2 \epsilon^2} = \frac{\hbar^2}{2\mu a_B^2}$ $a_B = \frac{\hbar^2 \epsilon}{\mu e^2}$



Cu_2O

